## A nti-K ondo regim e of charge transport through a double dot m olecule

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The conductance through a serial double dot structure for which the inter-dot tunneling is stronger than the tunneling to the leads is studied using the num erical density matrix renormalization group method and analytic arguments. When the dots are occupied by 1 or 3 electrons the usual K ondo peak is obtained. For the case in which 2 electrons occupy the molecule a singlet is formed. Nevertheless, the conductance in that case has a constant non-zero value, and might even be equal to the maximum conductance of  $2e^2$ =h for certain values of the molecule parameters. We show that this is the result of the subtle interplay between the symmetric and anti-symmetric orbitals of the molecule caused by interactions and interference.

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D ouble quantum dot devices have recently drawn much attention both for their relevance to possible technological applications such as qubits [1, 2, 3, 4, 5], as well as the light they shed on basic concepts such as the K ondo e ect and the Fano resonance [1, 6, 7, 8]. The double quantum dot molecule can be connected in parallel to the leads, such that electrons m ay tunnel from each dot to any lead. In this case one expects interference between paths going through each of the dots to play an important role in the transport through the molecule. The interplay between interference and interaction e ects such as C oulom b blockade, spin and orbitalK ondo e ects, is the subject of m any recent papers [1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11, 12].

In comparison, the transport through a serially connected molecule, for which electrons from the right lead can tunnel only to the right dot and vise versa, is expected to be much duller. At very low tem peratures one anticipates that for an odd lling of a molecule com posed of two identical dots the K ondo e ect will dom inate the conductance. If the tunneling between the dots is much weaker than the coupling of the dot to the lead an orbital K ondo e ect (where the two degenerate states are an electron occupying the left or right dot) is expected. In the opposite lim it a spin K ondo e ect will be observed (where the degenerate states are a spin up or down electron occupying the symmetric or anti-symmetric superposition of both dots orbitals). For a certain value of interm ediate tunneling between the dots a SU (4) K ondo e ect is expected. For even occupation of the molecule one may expect the usual Coulom b blockade scenario, ie, once the num ber of electron on the molecule is integer no conduction through it is expected.

This naive picture may be broken by the following scenario: Each of the two electrons is localized on a single dot and form s a K ondo singlet with the electrons of the corresponding leads [9]. Transport is then possible between the left and right K ondo state, and the conductance may even reach the maximum value of  $2e^2=h$ 

for certain values of the molecule parameters [10]. This state can be energetically favorable only if the gain from the form ation of a K ondo state (which is of order of the K ondo tem perature  $T_{\rm K}$ ) is larger than the loss of kinetic and interaction energy due to the localization of the electron on a single dot (i.e., the triplet-singlet energy separation). Since  $T_{\rm K}$  depends exponentially on the coupling of the dots to the leads, one expects this behavior only if the hopping between the dot and the lead is much larger than the inter-dot hopping.

In this paper we shall show that also in the opposite lim it where the inter-dot hopping is much larger than the hopping to the leads, nite conductance for the doubly occupied molecule of two serial dots is possible and may even reach the maximum value of  $2e^2 = h$ . Since in this state the ground state of the molecule is a singlet, this conductance is not connected to the K ondo e ect. Rather, this conductance stems from interactions in the molecule, which result in partial occupation of both the symmetric and anti-symmetric states. Thus both states can carry current even when the average occupation of the molecule is integer. It should be noted how ever that this current vanishes in the lim it when the sym m etric and anti-sym m etric states are degenerated - this lim it corresponds to two disconnected dots. On the other hand in the opposite lim it when the energy separation is large the situation is similar to the conventional Coulom b B lockade, i.e., the current should be sm all for any integer occupation. All in all there should be some optim al splitting between the two states, which corresponds to a maximum of the conductance. As we shall show the non-zero conductance valley is constant for a wide region of gate voltages and is only weakly dependent on the tem perature and external magnetic eld, which is very di erent than the typical K ondo behavior.

The serial double quantum dot molecule model is dened by the H am iltonian

$$H = H_{m olecule} + H_{leads} + H_{m ix} :$$
(1)

The H am iltonian, H  $_{m olecule}$ , of the double dot m olecule is given by

$$H_{m olecule} = \begin{array}{cccc} X & & & X \\ H_{m olecule} = \begin{array}{cccc} & & & & X \\ & & & & \\ &$$

where the energy level of each dot (with creation operator  $b_{1(2)}^{V}$  for an electron in the rst (second) dot with spin ), the intra-dot hopping matrix element t and the charging energies U for each dot and the mutual capacit ive coupling energy U<sup>0</sup>. By applying a gate voltage V<sub>g</sub> to the molecule one may change the dot's level to К. In principle also the hopping between the dots, t, m ay be changed by applying a side gate (as well as the hopping between the dot and the lead). For any realistic con guration one expects  $U > U^0$ . The in uence of an external magnetic eld h and chem icalpotential are included in the rst term of Eq. (2). The lead H am iltonian, H leads =  $j_{j} = "_{j} = L_{R}$   $a_{j}^{Y} a_{j} + (a_{j}^{Y} a_{j+1} + h x)$  and the tunneling between lead and molecule is described by  $H_{m ix} = V_{a_1 L} = (a_1^y b_1 + a_1^y b_2) + h c:. Here a_1^y$ is the creation operator in the i-th site of the = L(R)left (right) lead, the hopping in the leads is set to one and the hopping between the lead and dot is V.

It is useful to rst consider the eigenvalues and eigenvectors of a disconnected molecule, i.e., to diagonalize  $H_{m \text{ olecule}}$ . De ning the single particle basis as j+i =(jli + j2i) = 2 and ji = (jli j2i) = 2 (where jli; j2iare the orbitals of the rst and second dot), one can denote the many particle Hilbert space by the application  $b_2^{y}$  )= 2) and of the creation operators  $d_{+}^{y} = b_{1}^{y}$  $d^y = (b_1^y \quad b_2^y) = \frac{7}{2}$  on the vacuum juaci. Thus, for exam ple,  $j"; #i = d_{+}^{y} d_{+}^{y}$  jvaci and  $j"#; 0i = d_{+}^{y} d_{+}^{y}$  jvaci. The matrix corresponding to H  $_{\rm m\,o\,lecu\,le}$  is block-diagonal with respect to the number of electrons N (N m ay vary between zero and four) and each block may be diagonalized independently. The following lowest eigenvalues and eigenstates for each block are found: "( $\mathbb{N}$  = 0) = 0; yaci ; "(N = 1) = t; j ";0i and "(N = 1) = t;j#;0i (double degeneracy) ; " (N =  $2) = 2 ( ) + (U + U^{0}) = 2$   $(U - U^{0})^{2} + (4t)^{2} = 2; (1 + t)^{2} = 2; (1 + t)^$  $\int_{p}^{1} \frac{1 + [4t=(U \ U^{0})]^{2}}{1 + [4t=(U \ U^{0})]^{2}}$ 4t=(U U<sup>0</sup>)]<sup>2</sup>) <sup>1</sup>fj "#;0i +  $\int \frac{1}{1 + [4t=(U U^0)]^2} 4t=(U U^0)) j; "#ig ; "(N = 1)$  $3) = 3() + U + 2U^{0} + t; j #; "i and "(N = 3) =$  $3() + U + 2U^0$  t; j"#; #i (double degeneracy); and  $"(N = 4) = 4() + 2U + 4U^{0}; j"#; "#i.$ 

Generally, one expects that coupling the molecule to the leads will cause broadening of the molecule states, but as long as V < t the state of the molecule will continue to retain their identity. Thus one might predict the following behavior of the molecules occupation (i.e., number of electrons on the molecule) an function of . For > t the dot population N = 0. A round

t the population switches to N = 1. At  $(U + U^0) = 2 + (U - U^0)^2 + (4t)^2 = 2$  the popup = 2, w hile atU=2 3U<sup>0</sup>=2  $C: (U U^0)^2 + (4t)^2 = 2 + t$  it switches to N = 3. Finally  $U = 2U^0$  the molecule will be fully occupied. at. ;(2) A coording to the "orthodox" theory [13] one would expect a peak in the conductance each time when the population switches. Thus one would expect four peaks in the conductance as a function of at the values of the switches in the molecule population given previously. This consideration will not hold at zero tem perature and zero magnetic eld (T; h = 0), provided that K ondo physics will play an important role. Thus for odd occupancy of the molecule (N = 1;3), for which the ground state is degenerate, we expect to see a Kondo plateau in which the conductance is equal to  $2e^2=h$ . On the other hand for the N = 2 occupancy there are no degeneracies in the molecule ground state,

e.g., the singlet (S = 0) ground state is quite far away from the triplet state. Therefore naively one expects no conductance. Thus, at T = 0 we expect two broad conduction peaks separated by a zero conductance valley. The width of the K ondo conductance peaks are 2t+ (U + U<sup>0</sup>)=2  $(U - U^0)^2 + (4t)^2 = 2$ , while the width of the valley is  $2t + U^0 + \frac{P}{(U - U^0)^2 + (4t)^2}$ .

Once we attach the molecule to the leads, the problem becomes much more complicated W e compute the ground state for the interacting molecule attached to a couple of 1D leads using an extension of a DMRG m ethod previously used to calculate the ground state of a dot attached to leads [14]. The essence of the method is sim ilar to the regular DMRG for 1D systems [15]. Once we obtain the many-body ground state eigenvector Di of the entire system we can calculate the occupation of the j+i and j i orbitals of the molecule de ned as =  $h0 d^{y} d$   $f^{y}$  d  $f^{y}$  d  $f^{y}$  d n dot with each of the two dots' is coupled symmetrically to a corresponding lead, and the interactions don't explicitly break the symmetry, the Friedel sum rule in plies the relation  $g = \sin^2 ((n_+ - n_-)) + \sin^2 ((n_+ - n_+))$ in the usual way [16]. Thus, the occupations n determ ines the conductance.

In Fig. 1a we present the num erical results obtained for the conductance as function of the gate voltage () for di erent values of the inter-dot interaction U<sup>0</sup>, while U = 0.8,t = 0.2 and V = 0.1 are kept constant. The two broad K ondo peaks (for which g = 2) are very clear and their width corresponds to our expectation 2t+ (U + U<sup>0</sup>)=2  $(U - U^{0})^{2} + (4t)^{2}=2$  (see the inset of Fig. 1b) obtained for a disconnected m olecule. The coupling with the leads rounds the peaks, but does not signi cantly change their width. Thus, in the absence of interactions (U; U<sup>0</sup> = 0) there is no peak (the width is equal to zero), while for U = U<sup>0</sup> the width is simply U.

The surprise in Fig. 1a com es from the behavior of

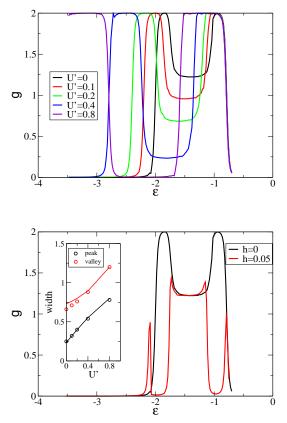


FIG.1: (a) C onductance, g, vs. gate voltage (level position), , for di erent values of the inter-dot interaction U<sup>0</sup>, while the on-site interaction U = 0.8, inter-dot hopping t = 0.2 and dot-lead coupling V = 0.1 are kept constant and no external m agnetic eld is applied.. (b) g, vs. in the presence of a m agnetic eld h = 0.05 com pared to g in the absence of such a eld. H ere U<sup>0</sup> = 0, and the other param eters are as in (a). Inset: the peak and valley width as function of U<sup>0</sup>. Sym bols correspond to the num erical results while lines to theory.

the valley. A though its width corresponds quite well to the expectation of  $2t + U^0 +$  $(U U^{0})^{2} + (4t)^{2}$ (see the inset of Fig. 1b) the conductance in the valley is constant and not necessarily equal to zero. The N = 2 state conductance is not suppressed by applying a magnetic eld. As seen in Fig. 1b, applying a magnetic eld that is enough to suppress the K ondo peaks of the N = 1 and N = 3 sectors, resulting in the expected four conductance peaks, does not change much the conductance at the N = 2 valley. This is expected since the ground state of the disconnected m olecule for the N = 2 sector is a singlet and does not couple to the external magnetic eld. Only for a magnetic eld  $h > (U^0 U) = 2 + (U U^0)^2 + (4t)^2 = 2 w$  ill the triplet excited state (j"";0i) cross the singlet state and the conductance will drop to zero. A lthough the conductance in the valley has som e super cial sim ilarities to the K ondo conductance (i.e., is constant for a wide range of gate voltages), the fact that the ground state in the molecule has no degeneracies rules out any kind of K ondo-like senarios.

In fact a wide region of alm ost constant conductance for double dots connected in series could be seen in the data presented in studies using slave boson form alism [17], and num erical renorm alization m ethods [18]. H ints of this behavior are also present in the study for 3 dots in the N = 2 and N = 4 regions [19]. N evertheless, the straight-forward expectation is that the conductance of the N = 2 region of the double dot m olecule is zero unless som e ferrom agnetic coupling between the dots w ill create a triplet ground state for N = 2 [20, 21], or when each dot is m ore strongly coupled to its lead than to each other, in which case a separate left and right K ondo state form and transport between these states is possible [9]. H ere none of these explanations is relevant.

The mechanism behind the conductance plateau of the N = 2 state of the molecule has to do with the in uence of the interaction on the ground state of the N =  $2 \sec$ tor. In the absence of interaction, the + state (j"#;0i) is full and thus can not conduct, while the state (D; "#i) is empty and thus also doesn't conduct. Due to interactions the molecule nds it favorable to occupy a superposition of both states and therefore neither of them are empty, and both, in principle may carry current. Since both states have an transmission phase di erence, there will be interference between the two paths, which is taken into account in the Friedel sum conductance  $g = \sin^2((n_+, n_+)) + \sin^2((n_+, n_+))$ . Thus when  $n_{+} = n$  destructive interference will occur and the conductance will be zero, while when  $j_{1+}$  n j = 1=2 m aximum conductance per spin of  $e^2 = h$  is obtained. P lugging in the values of  $n_+$  and  $n_-$  as function of t, U and U<sup>0</sup> previously calculated, we obtain the following expression for the valley plateau dim ensionless conductance:

$$g = 2\sin^{2} \frac{(1 [1 + [4t=(U U^{0})]^{2} + 4t=(U U^{0})]^{2})}{1 + [1 + [4t=(U U^{0})]^{2} + 4t=(U U^{0})]^{2}}$$
(3)

This prediction was tested by comparing it to the numerical results for the conduction in the middle of the valley, depicted in the upper part of Fig. 2. A reasonable agreement can be seen. According to Eq. (3) the conductance in the valley will be equal to its maximal value of 2 once the argument of the sin is equal to =2, i.e.,  $n_+$  n = 1=2. Thus, for

$$t = \frac{U U^{0}}{4 3};$$
 (4)

the valley conductance should be equal to 2 (if the molecule is asymmetrically coupled to the leads, i.e.,  $V_L \in V_R$  the valley height, as well as the K ondo peak height, will be  $8(V_L V_R)^2 = (V_L^2 + V_R^2)^2$ ). As can be seen in the lower panel in Fig. 2, for a double dot in which t is tuned to the value expressed in Eq. (4), the conduction for all molecule populations ranging between N = 1 and N = 3 is equal to 2. The conductance value of g 2

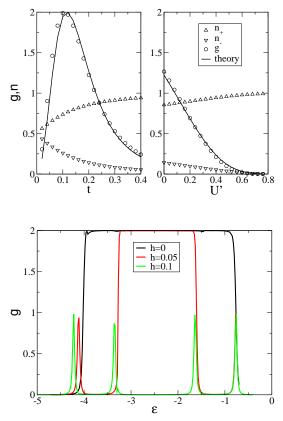


FIG.2: (upperpanel) C onductance at them iddle of the valley for U = 0.8 and V = 0.05: as function of twhile U<sup>0</sup> = 0 (left) and as function of U<sup>0</sup> with t = 0.2 (right). The symbols corresponding to the numerical results t quite well the line representing Eq. (3). (lower panel) C onductance as function of for V = 0.1, U = 2, U<sup>0</sup> = 0.4 and t = 0.23 and no external magnetic eld com pared to the conductance in the presence of a magnetic eld h = 0.05. W ith no magnetic eld g 2 for all molecule populations ranging between N = 1 and N = 3. W hen a weak magnetic eld is applied g 2 only for N = 2, while for a stronger eld 4 C oulom b blockade peaks are observed.

stems from two di erent processes. In the N = 1 and N = 3 regime it is the usual K ondo conductance while in the N = 2 it stems from the constructive interference between the conductance through the + and states. This can be clearly seen when an external magnetic eld is applied. The K ondo conductance is then suppressed, but the N = 2 state conductance isn't.

Tem perature is expected to have a very di erent inuence on the conductance for the di erent sectors of the gate voltage. As long as the molecule is in the K ondo regime (i.e., N = 1;3), the relevant energy scale is the K ondo tem perature,  $T_K$ , which depends exponentially on the tunneling coupling of the molecule to the lead (V). On the other hand, in the \valley" (N = 2) as long as inelastic e ects are ignored (in 1D systems both electron-electron and electron-phonon scattering are rather weak) the conductance will change signi – cantly only when  $k_B T$  is of order of the singlet-triplet separation  $k_B T$  (U<sup>0</sup> U)=2+  $p \frac{(U U^0)^2 + (4t)^2}{(U U^0)^2 + (4t)^2}=2$ .

In conclusion, the conductance through a strongly bound identical double dot molecule was studied. The gate voltage applied on the molecule changes its 11ing and therefore changes its conductance. Since the molecule is relatively weakly coupled to the leads, the num ber of electrons on the molecule is a good quantum number. For low temperatures (T <  $T_K$ ) odd llings (N = 1;3) lead to the usual K ondo conductance of  $2e^2 = h$ . For the even llings of N = 0;4 the conductance is equal to zero. The conductance for N = 2 is sensitive to the param eters of the molecule, and can assume values between 0 2e<sup>2</sup>=h. This behavior stems from the partial lling of both the symmetric and anti-symmetric orbitals due to interactions. Thus current lows through both orbitals and the conductance is the result of the interference between them . Thus, as function of the gate voltage a wide resonance tunneling plateau in the conductance appears, which is quite unsensative to tem perature and applied magnetic eld.

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